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Application No. 09/434,736
Amendment dated January 15, 2008

PATENT

Amendments to the Specification:

At column 3, after the paragraph ending on line 35 and before the paragraph beginning on line 36, please add the following paragraph:

Referring to Fig. 2A, in one embodiment of the present invention, a photoresist film is used to cover first insulating oxide layer 6. The photoresist film is then processed to create the contact pattern mask. Contact holes 30 are formed in first insulating oxide layer 6 as illustrated in Fig. 2A. The portion of contact holes 30 nearest gate electrode 5 or junction 2 are generally vertical. In some embodiments, such portions of the contact holes are at about a 90 degree angle to the top surface of silicon substrate 1. The upper portion of contact holes 30 are tapered as illustrated in Fig. 2A. In some embodiments, the taper extends from the center of contact holes 30 outward at approximately a 45 degree angle relative to the top surface of silicon substrate 1. In some embodiments, contact holes 30 are formed as illustrated in Fig. 2A using a combination of wet and dry etches. In a particular embodiment the process of forming contact holes 30 includes performance of a wet etch followed by a dry etch to form contact holes 30 as illustrated in Fig. 2A. In another embodiment, the process of forming contact holes 30 includes performance of a dry etch followed by a wet etch to form contact holes 30 as illustrated in Fig. 2A. In yet other embodiments, contact holes 30 as illustrated in Fig. 2A are formed using only a wet etch or a dry etch.